

# Contents

**Abstract** (in Chinese)

**Abstract** (in English)

**Acknowledgement**

**Table Captions**

**Figure Captions**

## **Chapter 1 Introduction**

1.1 Research Background of Copper Metallization for GaAs-based Devices.....	1
1.2 Overview of the Thesis.....	3
1.3 References.....	5

## **Chapter 2 InGaP/GaAs Heterostructure Grown by LP-MOCVD**

2.1 Introduction to LP-MOCVD System.....	7
2.1.1 LP-MOCVD System.....	8
a. Gas Handling System.....	8
b. Reactor Chamber.....	8
c. Heating System for Pyrolysis Temperature.....	9
d. Exhaust System and Safety Apparatus.....	9
2.2 MOCVD Epitaxy Theory of InGaP/GaAs Heterostructure.....	9
2.2.1 Starting Materials.....	10
2.2.2 Precursor Properties.....	11
2.2.3 Thermodynamics.....	12
2.2.4 Kinetics.....	12
2.2.5 Hydrodynamics and Mass Transport.....	12

2.2.6 Growth Rate Control Mechanism.....	13
a. Kinetically Controlled Region.....	14
b. Mass-Transport-Limited Region.....	14
c. Thermodynamically Controlled Region.....	14
2.2.7 The Growth Parameters for the Growth of InGaP/GaAs material System.....	14
2.2.8 Disordered and Ordered In <sub>0.49</sub> Ga <sub>0.51</sub> P Structure.....	15
2.3 Experimental Procedures.....	16
2.4 Results and Discussion.....	17
2.4.1 Characterization of the InGaP/GaAs Heterointerfaces.....	17
2.4.2 Photoluminescence and Raman Study of Ordered and Disordered InGaP .....	18
2.5 Conclusions.....	21
2.5 References.....	22



**Chapter 3 New Cu/Mo/Ge/Pd Ohmic Contacts on Highly-Doped  
n-GaAs for InGaP/GaAs Heterojunction Bipolar Transistors**

3.1 Introduction.....	38
3.2 Experimental .....	40
3.3 Discussion.....	42
3.3.1 Thermal Stability of the Cr/Cu/Mo/Ge/Pd/n <sup>+</sup> -GaAs Contact.....	42
3.3.2 Device Electrical Characteristics.....	44
3.4 Conclusions.....	46
3.5 References.....	47

**Chapter 4 Mechanism of Microstructure Evolution for the  
Cu/Ta/GaAs Structure after Thermal Annealing**

4.1 Introduction.....	60
4.2 Experimental Procedure.....	62
4.3 Results and Discussion.....	63
4.4 Conclusions.....	71
4.5 References.....	72
<b>Chapter 5 Conclusions.....</b>	<b>83</b>

**Vita (in Chinese)**

**Publication List**



# Table Captions

## Chapter 2

Table 2.1 Properties of the starting materials

## Chapter 3

Table 3.1 The proposed epitaxial structure of the InGaP/GaAs HBT



# Figure Captions

## Chapter 2

Figure 2.1. Schematic diagram of an MOCVD reactor and tube cross section.

Figure 2.2. Pyrolysis curves of TEGa.

Figure 2.3. TMIn decomposition ratio in three different carriers, H<sub>2</sub>, D<sub>2</sub> and He.

Figure 2.4. Pyrolysis curves of AsH<sub>3</sub>.

Figure 2.5. Pyrolysis curves of PH<sub>3</sub>.

Figure 2.6. The Cu-Pt type ordered structure of InGaP

Figure 2.7. A (400) double crystal rocking curve for a 0.5 $\mu$ m thick InGaP layer grown on a (100) oriented substrate at 650°C.

Figure 2.8. Room temperature photoluminescence spectrum of the InGaP layer on GaAs substrate grown at 650°C by LP-MOCVD (V/III=150).

Figure 2.9. Cross-sectional SEM image of InGaP/GaAs QWs with the rough interfaces due to the formation of InGaAsP

Figure 2.10 Cross-sectional SEM image of InGaP/GaAs QWs with the optimized switching sequence.

Figure 2.11 PL spectra of (a) ordered and (b) disordered InGaP.

Figure 2.12. Changes in the InGaP energy gap with growth temperature as measured by room temperature PL. The In mole fraction was kept constant.

Figure 2.13. Raman spectra for InGaP grown at 620 and 730°C.

## Chapter 3

Figure 3.1.1. Emitter mesa etch.

Figure 3.1.2. Base and collector mesa etch.

Figure 3.1.3. Mesa isolation.

Fig 3.1.4. Emitter and collector ohmic contact metal formation.

Fig 3.1.5 Base ohmic contact metal formation.

Fig 3.1.6 Silicon nitride passivation.

Fig 3.1.7 Contact via etch.

Fig 3.1.8 Interconnect line.

Fig.3.2. Sheet resistances of Cr/Cu/Mo/Ge/Pd/n<sup>+</sup>-GaAs after annealing at 300, 350 and 400°C for 30 min.

Fig.3.3. XRD results of Cr/Cu/Mo/Ge/Pd/n<sup>+</sup>-GaAs as-deposited and after annealing at various temperatures.

Fig.3.4. AES depth profiles of Cr/Cu/Mo/Ge/Pd/n<sup>+</sup>-GaAs after annealing at 350°C for 10 min.

Fig.3.5. Cross-sectional TEM micrograph of Cr/Cu/Mo/Ge/Pd/n<sup>+</sup>-GaAs after annealing at 350°C for 10 min.

Fig.3.6. Comparison of common-emitter I-V characteristics of InGaP/GaAs HBTs with Au/Ni/Ge/Au and Cu/Mo/Ge/Pd ohmic contacts.

Fig.3.7. Comparison of Gummel plots of InGaP/GaAs HBTs with Au/Ni/Ge/Au and Cu/Mo/Ge/Pd ohmic contacts.

Fig.3.8. Common-emitter I-V curves of HBT with Cu/Mo/Ge/Pd ohmic contact before and after annealing at 250°C for 24 h.

Fig.3.9. Current gain as function of stress time at constant I<sub>B</sub> for 4 ×

## Chapter 4

Fig. 4.1. Sheet resistances of the as-deposited sample and the samples after annealing at various temperatures.

Fig. 4.2. XRD patterns of the as-deposited sample and the samples after annealing at various temperatures.

Fig. 4.3. Auger depth profiles of the as-deposited sample and the samples after annealing at various temperatures.

Fig. 4.4. (a) Cross-sectional TEM image of the as-deposited  $\text{Ta}_2\text{N}/\text{Cu}/\text{Ta}/\text{GaAs}$  sample. (b) High-resolution TEM image obtained from the same sample after being thinned to smaller thickness. (c) Lattice image of Ta crystal. (d) FFT pattern of Ta.

Fig.4.5. Cross-sectional TEM image of the  $\text{Ta}_2\text{N}/\text{Cu}/\text{Ta}/\text{GaAs}$  sample after annealing at 500 °C for 30 min.



Fig. 4.6 (a) High-resolution TEM image obtained from the interface of the reaction area after annealing at 550 °C for 30 min. (b) High-resolution TEM image of the reaction area at Ta/GaAs interface. (c) Lattice image of  $\text{TaAs}_2$ . (d) FFT pattern of  $\text{TaAs}_2$ . (e) High-resolution TEM image of the reacted area at the Ta/Cu interface. (f) Lattice image of  $\text{Cu}_3\text{Ga}$ . (g) FFT pattern of  $\text{Cu}_3\text{Ga}$  grain.

Fig. 4.7. (a) Cross-sectional TEM image of the sample after annealing at 600 °C for 30 min. (b) Cross-sectional TEM image of the same sample at another area. (c) Enlarged TEM image of an area from (b). (d) Dark-field image of TaAs. (e) Dark-field image of  $\text{Cu}_3\text{Ga}$ . (f) Selected-area diffraction pattern of TaAs.

(g) Selected-area diffraction pattern of  $\text{Cu}_3\text{Ga}$ .

Fig. 4.8. (a)-(c) EDS spectra taken from sites A-C in Fig. 4.7(a), and (d) EDS spectrum taken from site D in Fig. 4.7(b).

